

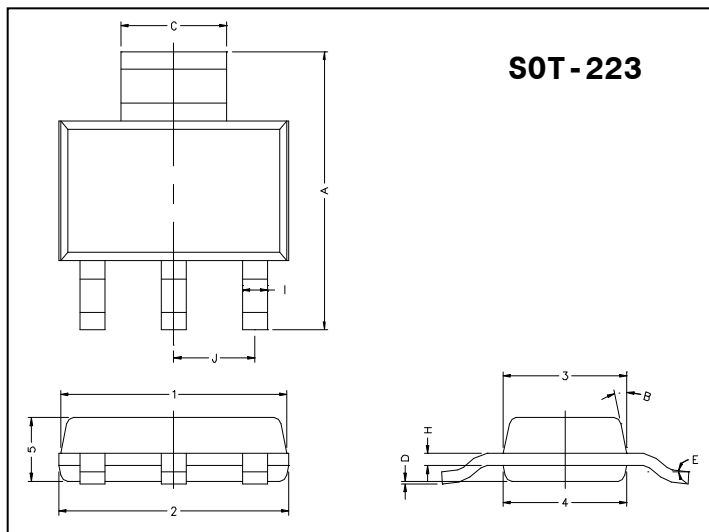
GL3906

PNP EPITAXIAL PLANAR TRANSISTOR

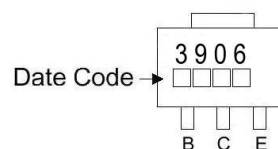
Description

The GL3906 is designed for general purpose Switching and Amplifier Applications.

Package Dimensions



Marking :



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 6.70 | 7.30 | B | 13° TYP. | |
| C | 2.90 | 3.10 | J | 2.30 REF. | |
| D | 0.02 | 0.10 | 1 | 6.30 | 6.70 |
| E | 0° | 10° | 2 | 6.30 | 6.70 |
| I | 0.60 | 0.80 | 3 | 3.30 | 3.70 |
| H | 0.25 | 0.35 | 4 | 3.30 | 3.70 |
| | | | 5 | 1.40 | 1.80 |

Absolute Maximum Ratings at Ta = 25°C

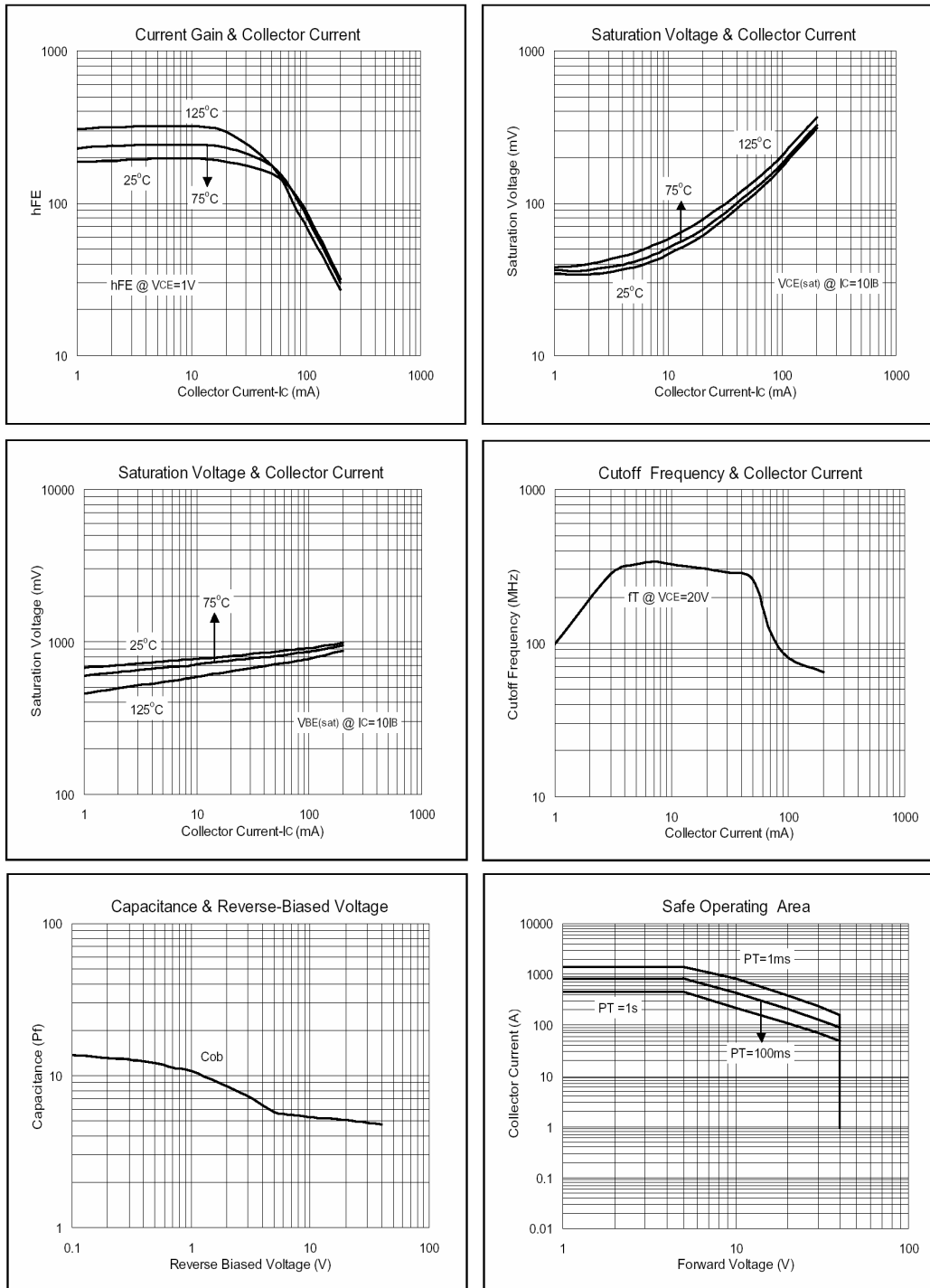
| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|----------|------|
| Junction Temperature | T _j | +150 | °C |
| Storage Temperature | T _{stg} | -55~+150 | °C |
| Collector to Base Voltage | V _{CB0} | -40 | V |
| Collector to Emitter Voltage | V _{CE0} | -40 | V |
| Emitter to Base Voltage | V _{EBO} | -5 | V |
| Collector Current | I _c | -200 | mA |
| Total Power Dissipation | P _D | 1.5 | W |

Characteristics at Ta = 25°C

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------------|-------|-------|-------|------|--|
| BV _{CB0} | -40 | - | - | V | I _C =-10uA |
| BV _{CE0} | -40 | - | - | V | I _C =-1mA |
| BV _{EBO} | -5 | - | - | V | I _E =-10uA |
| I _{CES} | - | - | -50 | nA | V _{CB} =-30V |
| I _{EBO} | - | - | -50 | nA | V _{EB} =-3V |
| V _{CE(sat)1} | - | - | -0.25 | V | I _C =-10mA, I _B =-1mA |
| V _{CE(sat)2} | - | -0.2 | -0.4 | V | I _C =-50mA, I _B =-5mA |
| V _{BE(sat)1} | -0.65 | - | -0.85 | V | I _C =-10mA, I _B =-1mA |
| V _{BE(sat)2} | - | -0.84 | -0.95 | V | I _C =-50mA, I _B =-5mA |
| hFE1 | 60 | - | - | | V _{CE} =-1V, I _C =-0.1mA |
| hFE2 | 80 | - | - | | V _{CE} =-1V, I _C =-1mA |
| hFE3 | 100 | - | 300 | | V _{CE} =-1V, I _C =-10mA |
| hFE4 | 60 | - | - | | V _{CE} =-1V, I _C =-50mA |
| hFE5 | 30 | - | - | | V _{CE} =-1V, I _C =-100mA |
| f _T | 250 | - | - | MHz | V _{CE} =-20V, I _E =-10mA, f=100MHz |
| C _{ob} | - | - | 4.5 | pF | V _{CB} =-5V, f=1MHz |

Note:Pulse test:PW<=300us, Duty Cycle<=2%

Characteristics Curve



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